



## SOT-23 Plastic-Encapsulate Transistors

### SS8550LT1 TRANSISTOR (PNP)

#### FEATURES

Power dissipation

$P_{CM}$ : 0.2 W ( $T_{amb}=25^{\circ}C$ )

Collector current

$I_{CM}$ : -1.5 A

Collector-base voltage

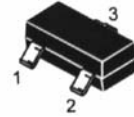
$V_{(BR)CBO}$ : -40 V

Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$

#### SOT-23

1. BASE
2. EMITTER
3. COLLECTOR



#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1mA, I_B = 0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -40V, I_E = 0$		-0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE} = -20V, I_B = 0$		-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$		-0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -100mA$	120	350	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -800mA$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800mA, I_B = -80mA$		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -800mA, I_B = -80mA$		-1.2	V
Transition frequency	$f_T$	$V_{CE} = -10V, I_C = -50mA$ $f = 30MHz$	100		MHz

#### CLASSIFICATION OF $h_{FE(1)}$

Rank	L	H
Range	120-200	200-350

DEVICE MARKING	SS8550LT1=Y2
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